











SN74CBTLV3253

SCDS039J-DECEMBER 1997-REVISED JANUARY 2018

# SN74CBTLV3253 Low-Voltage Dual 1-of-4 FET Multiplexer/Demultiplexer

#### **Features**

- Functionally Equivalent to QS3253
- $5-\Omega$  Switch Connection Between Two Ports
- Rail-to-Rail Switching on Data I/O Ports
- Ioff Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II

# **Applications**

- Video Broadcasting: IP-Based Multi-Format Transcoders
- Video Communications Systems

# 3 Description

The SN74CBTLV3253 device is a dual 1-of-4 highspeed FET multiplexer and demultiplexer. The low ON-state resistance of the switch allows connections to be made with minimal propagation delay.

The select (S0, S1) inputs control the data flow. The FET multiplexers/demultiplexers are disabled when the associated output-enable  $(\overline{OE})$  input is high.

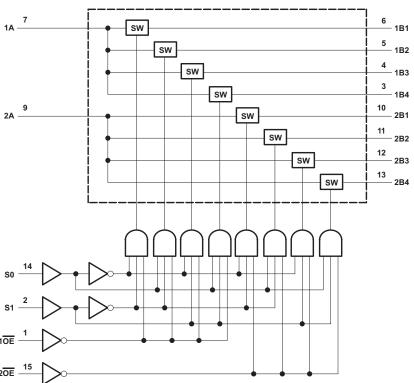
The SN74CBTLV3253 device is fully specified for partial-power-down applications using  $I_{\text{off}}$ . The  $I_{\text{off}}$ feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74CBTLV3253D	SOIC (16)	9.90 mm × 3.90 mm
SN74CBTLV3253DBQ	SSOP (16)	4.90 mm × 3.90 mm
SN74CBTLV3253DGV	TVSOP (16)	3.60 mm × 4.40 mm
SN74CBTLV3253RGY	VQFN (16)	4.00 mm × 3.50 mm
SN74CBTLV3253PW	TSSOP (16)	5.00 mm × 4.40 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

# Logic Diagram (Positive Logic)





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# **4 Revision History**

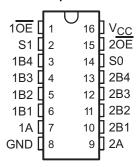
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision I (February 2014) to Revision J	Page
•	Changed the Thermal Information table	4
С	hanges from Revision H (February 2014) to Revision I	Page
•	Added Applications section, Device Information table, Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section	1
С	hanges from Revision G (February 2014) to Revision H	Page
•	Updated data sheet – no specific changes	1
С	hanges from Revision F (July 2012) to Revision G	Page
•	Deleted Ordering Information table.	1

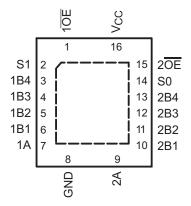


# 5 Pin Configuration and Functions

D, DBQ, DGV, or PW Package 16-Pin SOIC, SSOP, TVSOP, or TSSOP Top View



#### RGY Package 16-Pin VQFN Top View



#### **Pin Functions**

PIN		I/O	DESCRIPTION		
NAME	NO.	1/0	DESCRIPTION		
1 <del>OE</del>	1	I	Output Enable 1 Active-Low		
S1	2	I	Select Pin 1		
1B4	3	I/O	Channel 1 I/O 4		
1B3	4	I/O	Channel 1 I/O 3		
1B2	5	I/O	Channel 1 I/O 2		
1B1	6	I/O	Channel 1 I/O 1		
1A	7	I/O	Channel 1 common		
GND	8	_	Ground		
2A	9	I/O	Channel 2 common		
2B1	10	I/O	Channel 2 I/O 1		
2B2	11	I/O	Channel 2 I/O 2		
2B3	12	I/O	Channel 2 I/O 3		
2B4	13	I/O	Channel 2 I/O 4		
S0	14	I	Select Pin 0		
2 <del>OE</del>	15	I	Output Enable 2 Active-Low		
V <sub>CC</sub>	16	_	Power		

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### 6 Specifications

#### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
$V_{CC}$	Supply voltage		-0.5	4.6	V
$V_{IN}$	Control input voltage (2)	-0.5	4.6	V	
V <sub>I/O</sub>	Switch I/O voltage <sup>(2)</sup>		-0.5	4.6	V
I <sub>IK</sub>	Control input clamp current	V <sub>IN</sub> < 0		-50	mA
I <sub>I/OK</sub>	I/O port clamp current	V <sub>I/O</sub> < 0		<b>–</b> 50	mA
	Continuous current through $V_{CC}$ or GND			±128	mA
TJ	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

# 6.2 ESD Ratings

			VALUE	UNIT
	Flootroototio	Human Body Model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins (1)	+2000	V
V <sub>ESD</sub>	Electrostatic discharge	Charged-Device Model (CDM), per JEDEC specification JESD22-C101, all pins (2)	+1000	٧

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

# 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		2.3	3.6	V
V <sub>IH</sub>	Lligh lovel control input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		V
	High-level control input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2		V
	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7		
V <sub>IL</sub>	Low-level control input voltage	V <sub>CC</sub> = 2.7 V to 3.6 V		0.8	V
T <sub>A</sub>	Operating free-air temperature		-40	85	°C

All unused control inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, SCBA004.

### 6.4 Thermal Information

		SN74CBTLV3253					
	THERMAL METRIC <sup>(1)</sup>	D (SOIC)	DBQ (SSOP)	DGV (TVSOP)	PW (TSSOP)	RGY (VQFN)	UNIT
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	86.7	112.4	123.1	110.9	47.1	°C/W
R <sub>θJC(to</sub>	Junction-to-case (top) thermal resistance	47.8	63.6	48.7	45.8	58.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	43.7	54.8	54.9	56.0	24.0	°C/W
ΨЈТ	Junction-to-top characterization parameter	12.3	17.0	5.2	5.4	1.8	°C/W
ΨЈВ	Junction-to-board characterization parameter	43.5	54.4	54.3	55.4	24.0	°C/W
R <sub>θJC(b</sub> ot)	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	n/a	9.6	°C/W

 For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

<sup>(2)</sup> The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



#### 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PAR	AMETER		TEST CONDITION	S	MIN	TYP <sup>(1)</sup>	MAX	UNIT
$V_{IK}$		$V_{CC} = 3 V$ ,	$I_I = -18 \text{ mA}$				-1.2	V
I <sub>I</sub>		$V_{CC} = 3.6 \text{ V},$	$V_I = V_{CC}$ or GND	$V_{I} = V_{CC}$ or GND			±1	μΑ
I <sub>off</sub>		$V_{CC} = 0$ ,	$V_I$ or $V_O = 0$ to 3.6 V				15	μΑ
I <sub>CC</sub>		V <sub>CC</sub> = 3.6 V,	$I_{O} = 0$ ,	$V_I = V_{CC}$ or GND			10	μΑ
$\Delta I_{CC}^{(2)}$	Control inputs	V <sub>CC</sub> = 3.6 V,	One input at 3 V,	Other inputs at V <sub>CC</sub> or GND			300	μA
C <sub>i</sub>	Control inputs	V <sub>I</sub> = 3 V or 0				3		pF
•	A port	V 2 V 2 T 0	OF V			20.5		
$C_{io(OFF)}$	B port	$V_0 = 3 \text{ V or } 0,$	OE = V <sub>CC</sub>			5.5		pF
			I <sub>I</sub> = 64 mA		5	8		
		$V_{CC} = 2.3 \text{ V},$ TYP at $V_{CC} = 2.5 \text{ V}$	$V_I = 0$	I <sub>I</sub> = 24 mA		5	8	
(3)		111 at v <sub>CC</sub> = 2.5 v	V <sub>I</sub> = 1.7 V,	I <sub>I</sub> = 15 mA		27	40	0
r <sub>on</sub> (3)				I <sub>I</sub> = 64 mA		5	7	Ω
		V <sub>CC</sub> = 3 V	V <sub>I</sub> = 0	I <sub>I</sub> = 24 mA		5	7	
			$V_1 = 2.4 V$ ,	I <sub>I</sub> = 15 mA		10	15	

### 6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

PARAMETER	FROM	TO (OUTPUT)	V <sub>CC</sub> = 2. ± 0.2	5 V V	V <sub>CC</sub> = 3. ± 0.3	.3 V V	UNIT
	(INPUT)	` ,	MIN	MAX	MIN	MAX	
	A or B <sup>(1)</sup>	B or A		0.15		0.25	20
t <sub>pd</sub>	S	A or B	1	6.8	1	5.5	ns
t <sub>en</sub>	S	A or B	1	4.3	1	4	ns
t <sub>dis</sub>	S	A or B	1	5.1	1	5.5	ns
t <sub>en</sub>	ŌĒ	A or B	1	5	1	4.8	ns
t <sub>dis</sub>	ŌĒ	A or B	1	5.5	1	5.4	ns

<sup>(1)</sup> The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

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All typical values are at  $V_{CC}$  = 3.3 V (unless otherwise noted),  $T_A$  = 25°C. This is the increase in supply current for each input that is at the specified voltage level, rather than  $V_{CC}$  or GND.

Measured by the voltage drop between the A and the B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.



# 6.7 Typical Characteristics

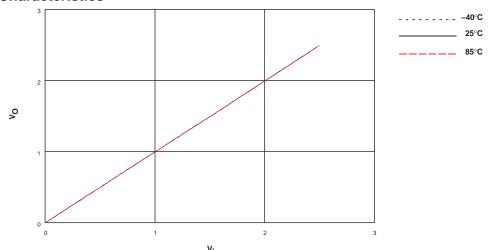
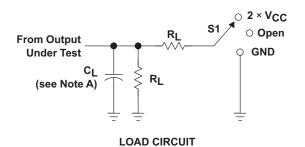


Figure 1.  $V_0$  vs  $V_I$ ,  $V_{CC}$  = 2.5 V

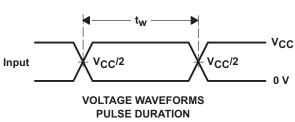


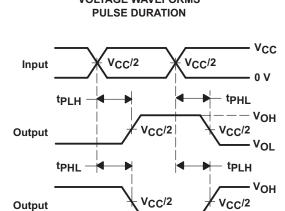
### 7 Parameter Measurement Information



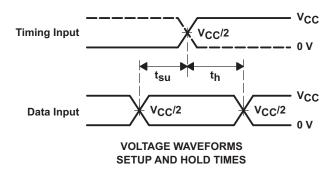
TEST	S1
tPLH/tPHL	Open
tPLZ/tPZL	2 × V <sub>CC</sub>
tPHZ/tPZH	GND

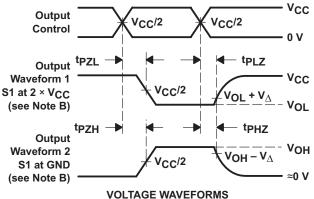
V <sub>CC</sub>	CL	RL	${f v}_{\Delta}$
2.5 V ±0.2 V	30 pF	<b>500</b> Ω	0.15 V
3.3 V ±0.3 V	50 pF	<b>500</b> Ω	0.3 V





VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS





ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

Figure 2. Test Circuit and Voltage Waveforms

VOL



### 8 Detailed Description

#### 8.1 Overview

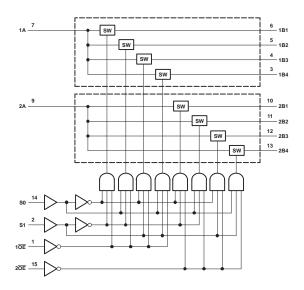
The SN74CBTLV3253 device is a dual 1-of-4 high-speed FET multiplexer/demultiplexer. The low ON-state resistance of the switch allows connections to be made with minimal propagation delay.

The select (S0, S1) inputs control the data flow. The FET multiplexers and demultiplexers are disabled when the associated output-enable  $(\overline{OE})$  input is high.

The SN74CBTLV3253 device is fully specified for partial-power-down applications using  $I_{\text{off}}$ . The  $I_{\text{off}}$  feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

To ensure the high-impedance state during power up or power down,  $\overline{\text{OE}}$  should be tied to  $V_{\text{CC}}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

### 8.2 Functional Block Diagram



### 8.3 Feature Description

The SN74CBTLV3253 device is functionally equivalent to the QS3253 and has a  $5-\Omega$  switch connection between two ports

It also has rail-to-rail switching on data I/O ports as well as I<sub>off</sub> supporting partial-power-down mode operation

#### 8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74CBTLV3253.

Table 1. Function Table (Each Multiplexer/Demultiplexer)

	•	-	-			
	INPUTS	FUNCTION				
ŌĒ	<b>S1</b>	S0	FONCTION			
L	L	L	A port = B1 port			
L	L	Н	A port = B2 port			
L	Н	L	A port = B3 port			
L	Н	Н	A port = B4 port			
Н	Х	X	Disconnect			



# **Application and Implementation**

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### 9.1 Application Information

The SN74CBTLV3253 can be used to multiplex and demultiplex up to 2 channels simultaneously in a 4:1 configuration. The application shown here is a 2-bit bus being multiplexed between two devices, the OE and S pins are used to control the chip from the bus controller. This is a very generic example, and could apply to many situations.

### 9.2 Typical Application

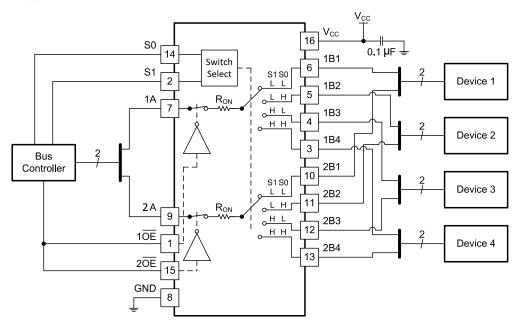


Figure 3. Typical Application of the SN74CBTLV3253

#### 9.2.1 Design Requirements

The 0.1µF capacitor should be placed as close as possible to the device.

#### 9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
  - For specified high and low levels, see V<sub>IH</sub> and V<sub>IL</sub> in Recommended Operating Conditions.
  - Inputs and outputs are overvoltage tolerant slowing them to go as high as 4.6 V at any valid V<sub>CC</sub>.
- 2. Recommended Output Conditions:
  - Load currents should not exceed ±128 mA per channel.
- 3. Frequency Selection Criterion:
  - Added trace resistance/capacitance can reduce maximum frequency capability; use layout practices as directed in Layout.

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### **Typical Application (continued)**

#### 9.2.3 Application Curve

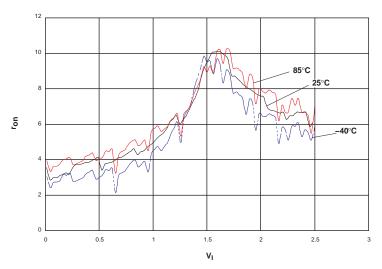


Figure 4.  $r_{on}$  vs  $V_I$ ,  $V_{CC} = 2.5 \text{ V}$ 

# 10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Recommended Operating Conditions* table.

Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- $\mu F$  bypass capacitor is recommended. If multiple pins are labeled  $V_{CC}$ , then a 0.01- $\mu F$  or 0.022- $\mu F$  capacitor is recommended for each  $V_{CC}$  because the  $V_{CC}$  pins are tied together internally. For devices with dual-supply pins operating at different voltages, for example  $V_{CC}$  and  $V_{DD}$ , a 0.1- $\mu F$  bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1  $\mu F$  and 1  $\mu F$  are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.



### 11 Layout

### 11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 5 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

#### 11.2 Layout Example

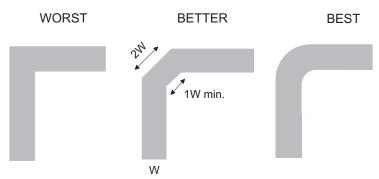


Figure 5. Trace Example

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### 12 Device and Documentation Support

#### 12.1 Documentation Support

#### 12.1.1 Related Documentation

For related documentation, see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004

#### 12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 12.3 Trademarks

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

#### 12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### 12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

### 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





24-Aug-2018

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing		Package Qty	Eco Plan	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
74CBTLV3253PWRG4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL253	Samples
SN74CBTLV3253D	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3253	Samples
SN74CBTLV3253DBQR	ACTIVE	SSOP	DBQ	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL253	Samples
SN74CBTLV3253DE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3253	Samples
SN74CBTLV3253DGVR	ACTIVE	TVSOP	DGV	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL253	Samples
SN74CBTLV3253DR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3253	Samples
SN74CBTLV3253DRE4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3253	Samples
SN74CBTLV3253PW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL253	Samples
SN74CBTLV3253PWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL253	Samples
SN74CBTLV3253RGYR	ACTIVE	VQFN	RGY	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL253	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE**: TI has discontinued the production of the device.

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



# PACKAGE OPTION ADDENDUM

24-Aug-2018

- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

# PACKAGE MATERIALS INFORMATION

www.ti.com 18-Jan-2018

# TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CBTLV3253DBQR	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
SN74CBTLV3253DGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CBTLV3253DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74CBTLV3253PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CBTLV3253RGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1

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\*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74CBTLV3253DBQR	SSOP	DBQ	16	2500	340.5	338.1	20.6
SN74CBTLV3253DGVR	TVSOP	DGV	16	2000	367.0	367.0	35.0
SN74CBTLV3253DR	SOIC	D	16	2500	333.2	345.9	28.6
SN74CBTLV3253PWR	TSSOP	PW	16	2000	367.0	367.0	35.0
SN74CBTLV3253RGYR	VQFN	RGY	16	3000	367.0	367.0	35.0



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.







- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
- 4. This dimension does not include interlead flash.5. Reference JEDEC registration MO-137, variation AB.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
- G. Package complies to JEDEC MO-241 variation BA.



# RGY (R-PVQFN-N16)

### PLASTIC QUAD FLATPACK NO-LEAD

#### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

Exposed Thermal Pad Dimensions

4206353-3/P 03/14

NOTE: All linear dimensions are in millimeters



# RGY (R-PVQFN-N16)

# PLASTIC QUAD FLATPACK NO-LEAD



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="https://www.ti.com">http://www.ti.com</a>.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



# D (R-PDS0-G16)

# PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



# D (R-PDSO-G16)

# PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





SMALL OUTLINE PACKAGE



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



# DGV (R-PDSO-G\*\*)

#### **24 PINS SHOWN**

#### **PLASTIC SMALL-OUTLINE**



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.

D. Falls within JEDEC: 24/48 Pins – MO-153 14/16/20/56 Pins – MO-194

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